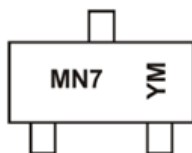


Marking Information



MN7 = Product Type Marking Code
 YM = Date Code Marking
 Y or \bar{Y} = Year (ex: I = 2021)
 M = Month (ex: 9 = September)

Date Code Key

| Year | 2021 | 2022 | 2023 | 2024 | 2025 | 2026 | 2027 | 2028 | 2029 | 2030 | 2031 | 2032 |
|------|------|------|------|------|------|------|------|------|------|------|------|------|
| Code | I | J | K | L | M | N | O | P | R | S | T | U |

| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
|-------|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|
| Code | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | O | N | D |

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

| Characteristic | | | Symbol | Value | Units |
|--|-----------------------|--|----------|------------|-------|
| Drain-Source Voltage | | | V_{DS} | 30 | V |
| Gate-Source Voltage | | | V_{GS} | ± 20 | V |
| Continuous Drain Current (Note 5) $V_{GS} = 10\text{V}$ | Steady State | $T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$ | I_D | 2.5 2.0 | A |
| Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$ | Steady State | $T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$ | I_D | 3.3 2.7 | A |
| Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$ | $t \leq 10\text{sec}$ | $T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$ | I_D | 3.8 3.1 | A |
| Continuous Drain Current (Note 6) $V_{GS} = 4.5\text{V}$ | Steady State | $T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$ | I_D | 2.7 2.1 | A |
| Pulsed Drain Current (Note 7) | | | I_{DM} | 25 | A |

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

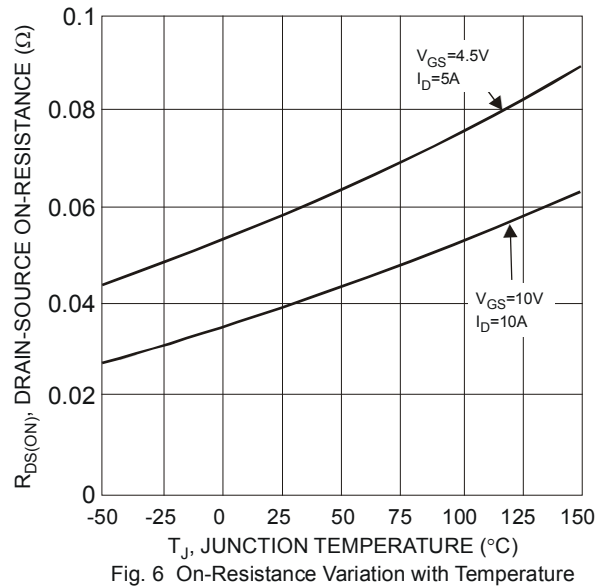
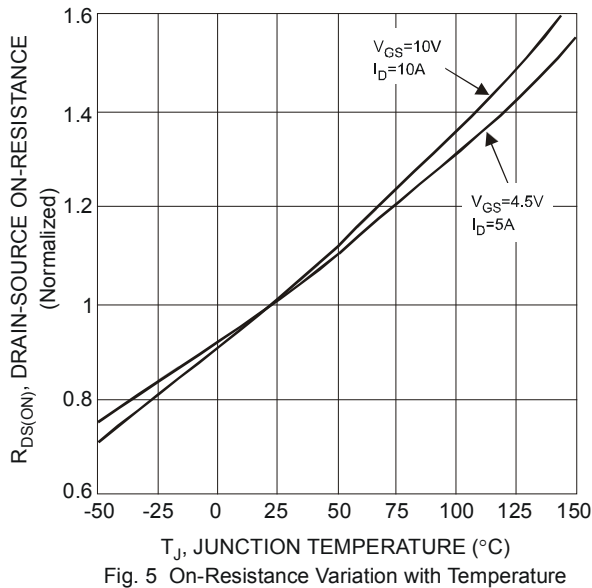
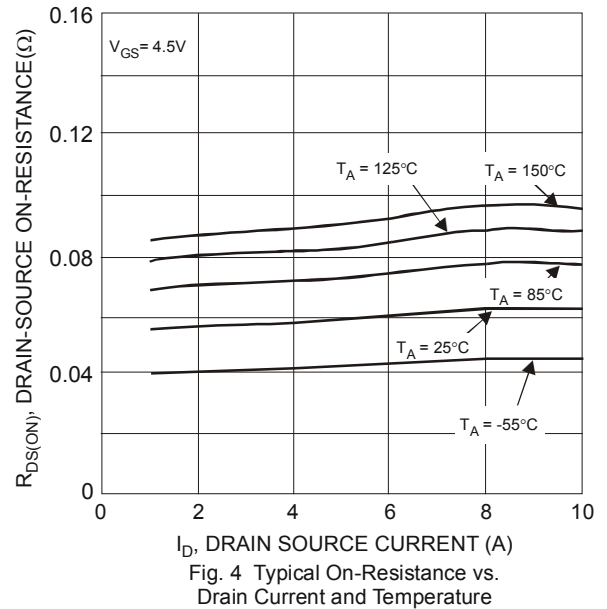
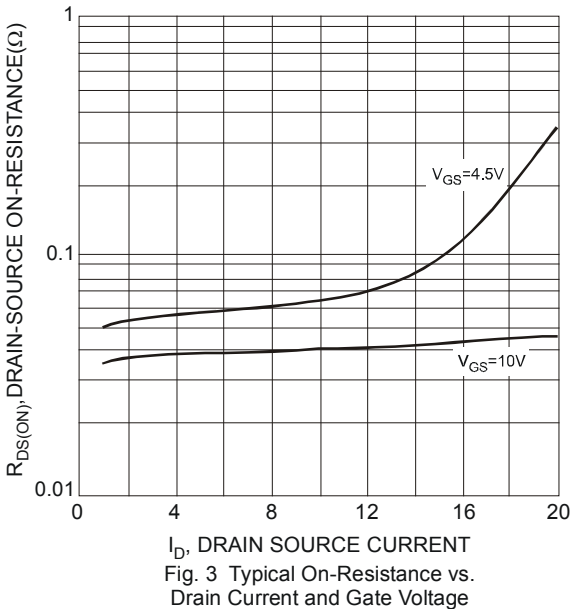
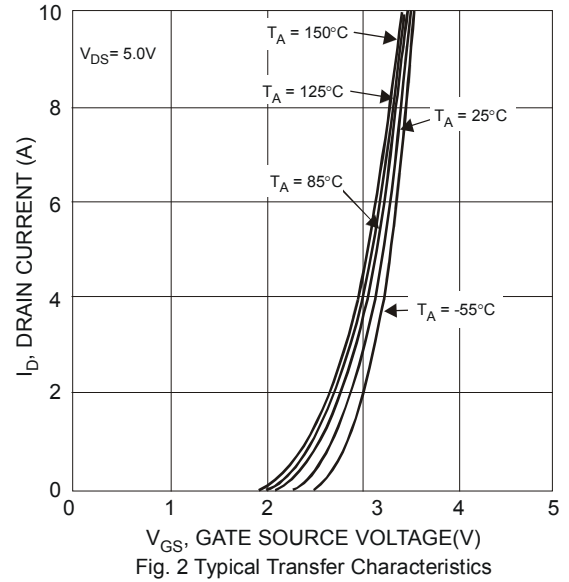
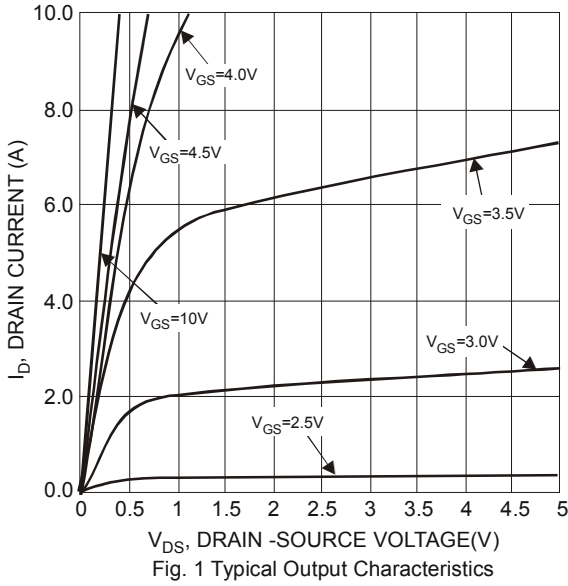
| Characteristic | Symbol | Value | Units |
|--|-----------------|-------------|--------------------|
| Total Power Dissipation (Note 5) | P_D | 0.74 | W |
| Thermal Resistance, Junction to Ambient (Note 5) | $R_{\theta JA}$ | 173.4 | $^\circ\text{C/W}$ |
| Total Power Dissipation (Note 6) | P_D | 1.3 | W |
| Thermal Resistance, Junction to Ambient (Note 6) | $R_{\theta JA}$ | 99.1 | $^\circ\text{C/W}$ |
| Total Power Dissipation (Note 6) $t \leq 10\text{sec}$ | P_D | 1.8 | W |
| Thermal Resistance, Junction to Ambient (Note 6) $t \leq 10\text{sec}$ | $R_{\theta JA}$ | 72 | $^\circ\text{C/W}$ |
| Operating and Storage Temperature Range | T_J, T_{STG} | -55 to +150 | $^\circ\text{C}$ |

Notes: 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, on 1inch square copper plate
 7. Device mounted on minimum recommended pad layout test board, 10 μs pulse duty cycle = 1%

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|---|--------------|-----|-------|-----------|------------|--|
| OFF CHARACTERISTICS (Note 8) | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | 30 | - | - | V | $V_{GS} = 0V, I_D = 250\mu A$ |
| Zero Gate Voltage Drain Current @ $T_C = +25^\circ\text{C}$ | I_{DSS} | - | - | 1.0 | μA | $V_{DS} = 30V, V_{GS} = 0V$ |
| Gate-Source Leakage | I_{GSS} | - | - | ± 100 | nA | $V_{GS} = \pm 20V, V_{DS} = 0V$ |
| ON CHARACTERISTICS (Note 8) | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | 1.0 | - | 3.0 | V | $V_{DS} = V_{GS}, I_D = 250\mu A$ |
| Static Drain-Source On-Resistance | $R_{DS(on)}$ | - | 54 | 73 | m Ω | $V_{GS} = 10V, I_D = 3.1A$ |
| | | - | 88 | 110 | | $V_{GS} = 4.5V, I_D = 2A$ |
| Forward Transfer Admittance | $ Y_{fs} $ | - | 4.8 | - | mS | $V_{DS} = 10V, I_D = 3.1A$ |
| Diode Forward Voltage (Note 6) | V_{SD} | - | 0.75 | 1.0 | V | $V_{GS} = 0V, I_S = 1A$ |
| DYNAMIC CHARACTERISTICS (Note 9) | | | | | | |
| Input Capacitance | C_{iss} | - | 305.8 | - | pF | $V_{DS} = 15V, V_{GS} = 0V, f = 1.0MHz$ |
| Output Capacitance | C_{oss} | - | 39.9 | - | pF | |
| Reverse Transfer Capacitance | C_{rss} | - | 39.5 | - | pF | |
| Gate Resistance | R_g | - | 1.4 | - | Ω | $V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$ |
| Total Gate Charge ($V_{GS} = 4.5V$) | Q_g | - | 4.1 | - | nC | $V_{GS} = 10V, V_{DS} = 10V, I_D = 3A$ |
| Total Gate Charge ($V_{GS} = 10V$) | Q_g | - | 8.6 | - | nC | |
| Gate-Source Charge | Q_{gs} | - | 1.2 | - | nC | |
| Gate-Drain Charge | Q_{gd} | - | 1.5 | - | nC | |
| Turn-On Delay Time | $t_{D(on)}$ | - | 2.6 | - | ns | $V_{DD} = 15V, V_{GS} = 10V, R_L = 47\Omega, R_G = 3\Omega,$ |
| Turn-On Rise Time | t_r | - | 4.6 | - | ns | |
| Turn-Off Delay Time | $t_{D(off)}$ | - | 13.1 | - | ns | |
| Turn-Off Fall Time | t_f | - | 2.5 | - | ns | |

Notes: 8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.



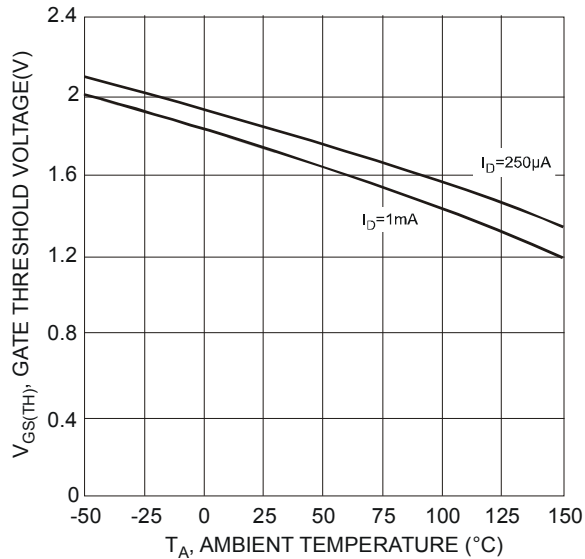


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

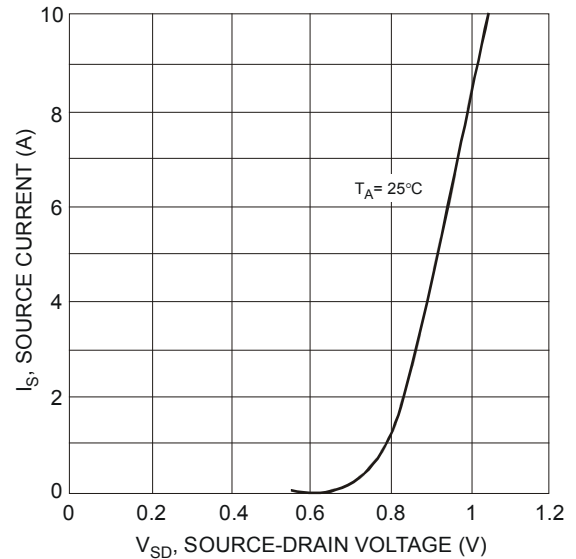


Fig. 8 Diode Forward Voltage vs. Current

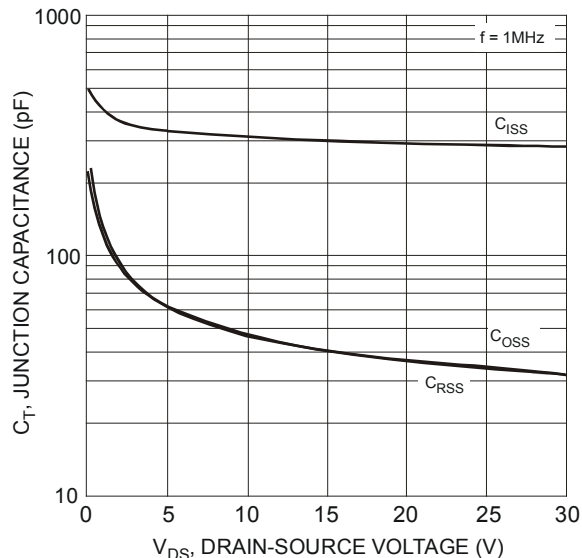


Fig. 9 Typical Junction Capacitance

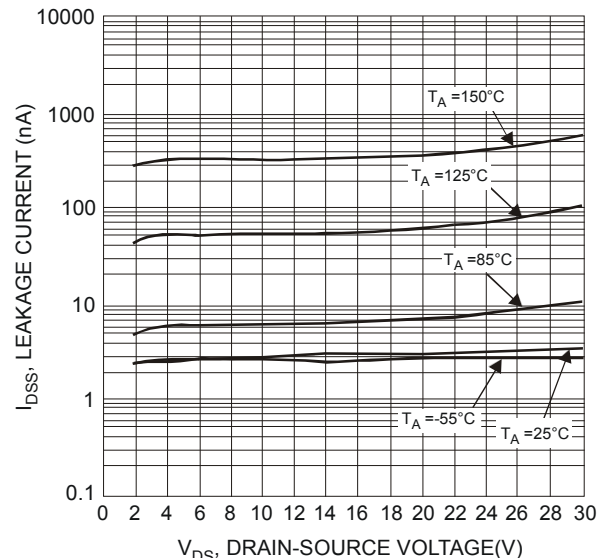


Fig. 10 Typical Drain-Source Leakage Current vs. Voltage

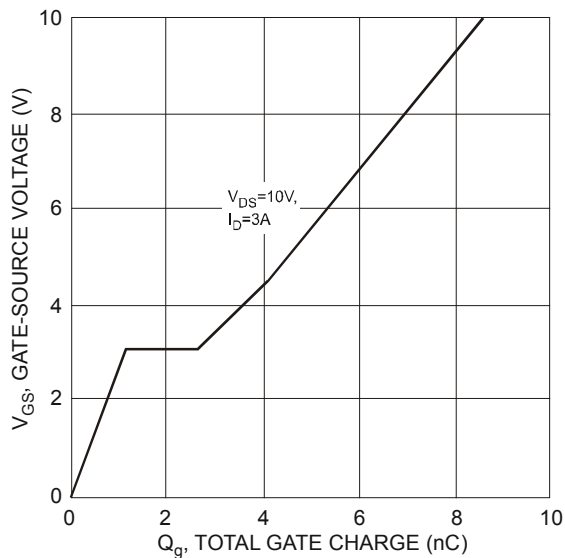
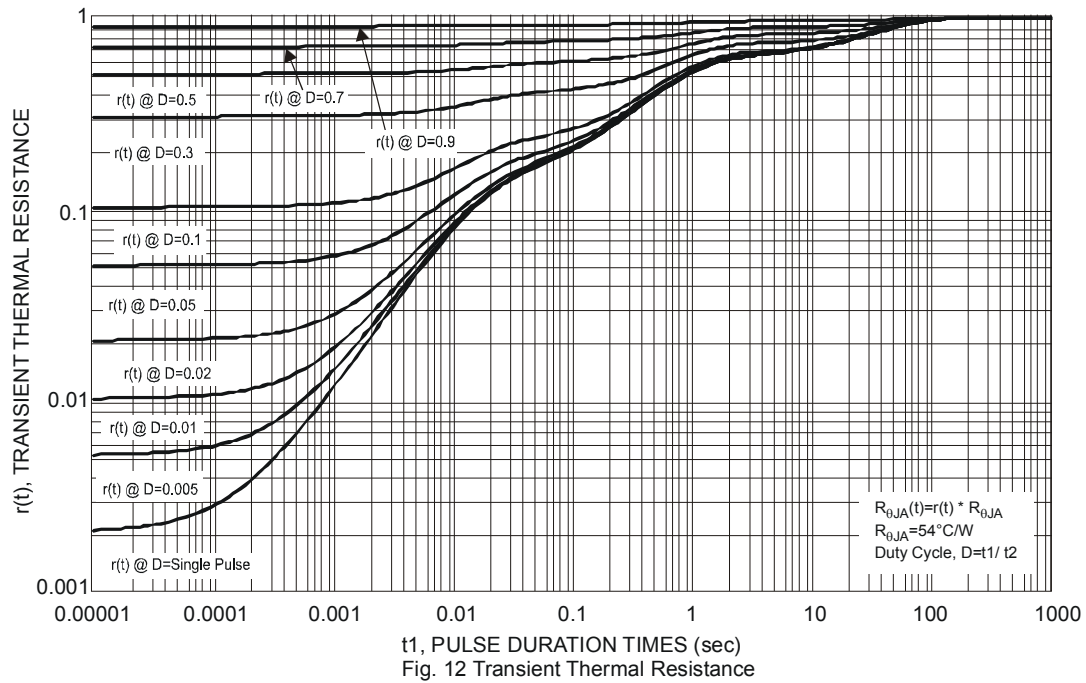


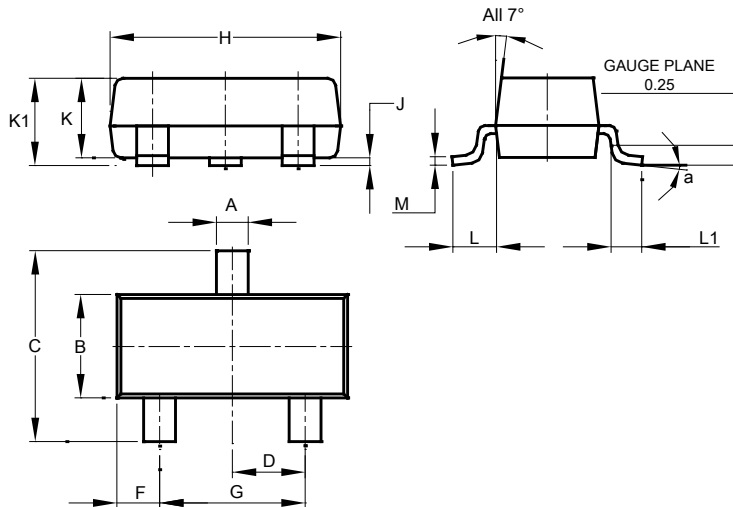
Fig. 11 Gate-Charge Characteristics



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23

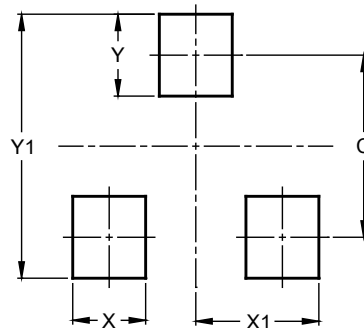


| SOT23 | | | |
|----------------------|-------|-------|-------|
| Dim | Min | Max | Typ |
| A | 0.37 | 0.51 | 0.40 |
| B | 1.20 | 1.40 | 1.30 |
| C | 2.30 | 2.50 | 2.40 |
| D | 0.89 | 1.03 | 0.915 |
| F | 0.45 | 0.60 | 0.535 |
| G | 1.78 | 2.05 | 1.83 |
| H | 2.80 | 3.00 | 2.90 |
| J | 0.013 | 0.10 | 0.05 |
| K | 0.890 | 1.00 | 0.975 |
| K1 | 0.903 | 1.10 | 1.025 |
| L | 0.45 | 0.61 | 0.55 |
| L1 | 0.25 | 0.55 | 0.40 |
| M | 0.085 | 0.150 | 0.110 |
| a | 0° | 8° | -- |
| All Dimensions in mm | | | |

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23



| Dimensions | Value (in mm) |
|------------|---------------|
| C | 2.0 |
| X | 0.8 |
| X1 | 1.35 |
| Y | 0.9 |
| Y1 | 2.9 |

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